



### **60V N-CHANNEL ENHANCEMENT MODE MOSFET** PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	Rds(on) max	I <sub>D MAX</sub> Tc = +25°C	
60V	1.5mΩ @ V <sub>GS</sub> = 10V	215A	

### **Description and Applications**

This new generation N-Channel enhancement mode MOSFET is designed to minimize RDS(ON) yet maintain superior switching performance. This device is ideal for use in power management and load switch.

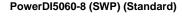
- **Engine Management Systems**
- **Body Control Electronics**
- **DC-DC Converters**

#### **Features**

- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- High Conversion Efficiency
  - Low RDS(ON) Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

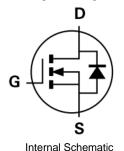
- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

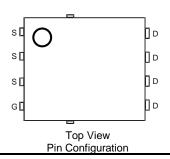












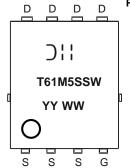
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT61M5SPSW-13	PowerDI5060-8 (SWP) (Standard)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



#### PowerDI5060-8 (SWP) (Standard)

] | = Manufacturer's Marking T61M5SSW = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 20 = 2020) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



# **Maximum Ratings** (@ $T_C = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Proin Correct V 40V (Note C)	T <sub>C</sub> = +25°C	I <sub>D</sub>	215	Α
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	Tc = +70°C		170	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	215	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Ірм	860	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Ism	860	Α
Avalanche Current, L=1mH		las	35.8	Α
Avalanche Energy, L=1mH		E <sub>AS</sub>	640.8	mJ

### Thermal Characteristics (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	<u>.</u>	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P <sub>D</sub>	139	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θ</sub> JC	0.9	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

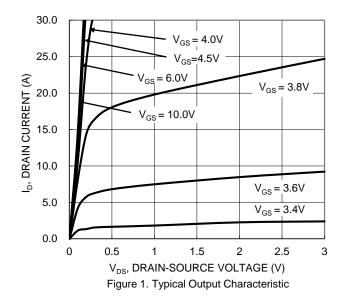
# **Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

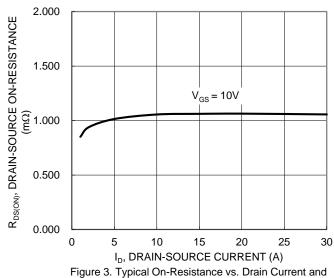
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	Vgs = ±20V, Vps = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	2	_	4	٧	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)	1	1.1	1.5	mΩ	Vgs = 10V, ID = 30A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	Ciss	1	8306	_		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss		2735	_	pF		
Reverse Transfer Capacitance	Crss		184	_			
Gate Resistance	$R_g$	_	3.0	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	130.6	_		V <sub>DS</sub> = 30V, I <sub>D</sub> = 30A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Qgs	_	30.4	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	28.1	_			
Turn-On Delay Time	td(on)	_	11.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{g} = 3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	28.5	_	20		
Turn-Off Delay Time	tD(OFF)	_	86.2	_	ns		
Turn-Off Fall Time	tF	_	47.6	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	70.4	_	ns	1 004 11/14 1004/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	1	127	_	nC	-I <sub>F</sub> = 30A, di/dt = 100A/μs	

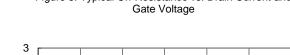
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

- Thermal resistance from junction to soldering point (on the exposed drain pad).
   Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.









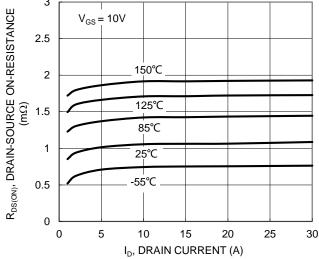


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

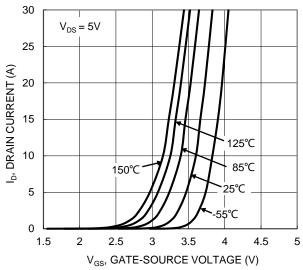


Figure 2. Typical Transfer Characteristic

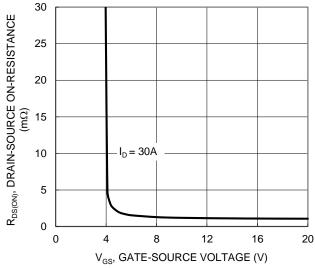


Figure 4. Typical Transfer Characteristic

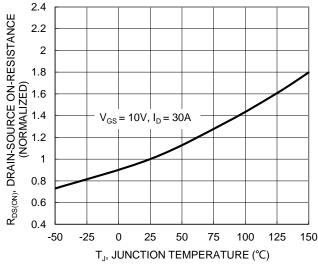


Figure 6. On-Resistance Variation with Temperature





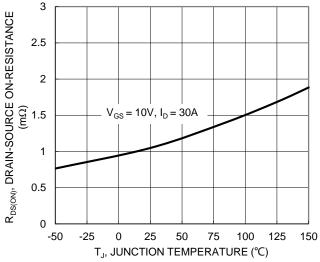


Figure 7. On-Resistance Variation with Temperature

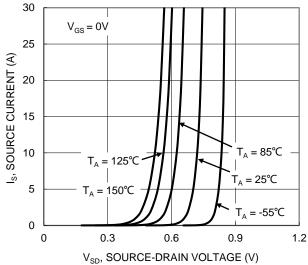
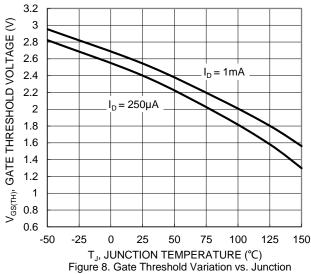


Figure 9. Diode Forward Voltage vs. Current



Temperature

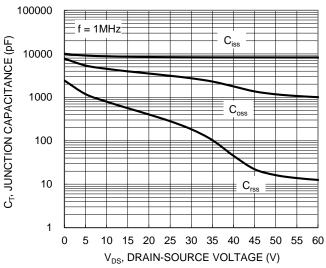


Figure 10. Typical Junction Capacitance

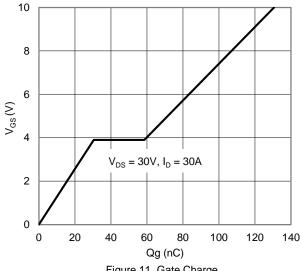
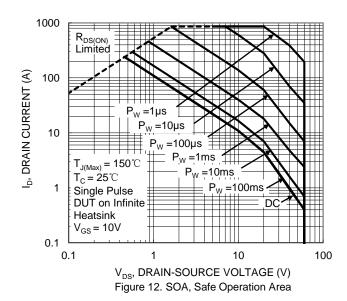


Figure 11. Gate Charge





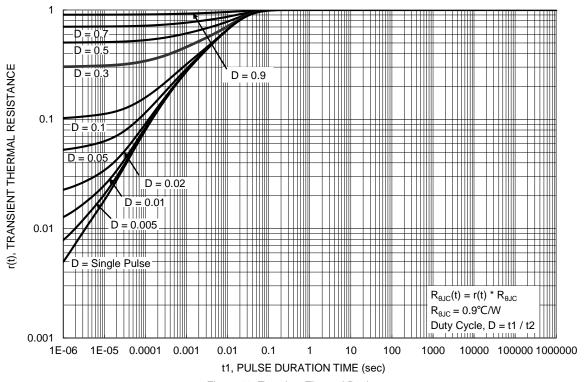


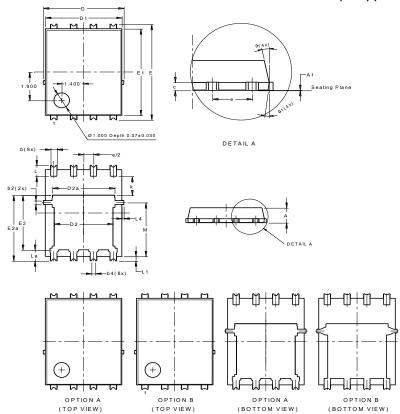
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (SWP) (Standard)

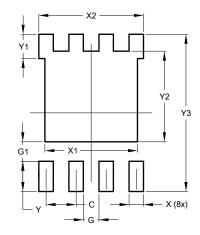


PowerDI5060-8 (SWP)					
(Standard)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4		).25REF	-		
С	0.230	0.330	0.277		
D	5	.15 BS0	2		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78 4.18		3.98		
Е	6	.40 BS0	$\sim$		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC			
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (SWP) (Standard)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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